

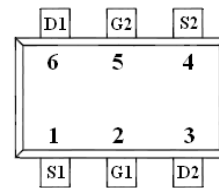
➤ General Description

This PAN3034L Dual N-Channel enhancement mode power field effect transistor is the high density trench technology and this advanced technology can provide excellent $R_{ds(On)}$ performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

➤ Feature

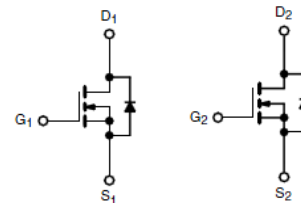
- Low Offset (Error) Voltage
- Low-Voltage Operation
- High-Speed Circuits
- Low Battery Voltage Operation
- SOT-563 package design

➤ SOT-563



➤ Application

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories
- Battery Operated Systems
- Power Supply Converter Circuits
- Load/Power Switching Smart Phones, Pagers



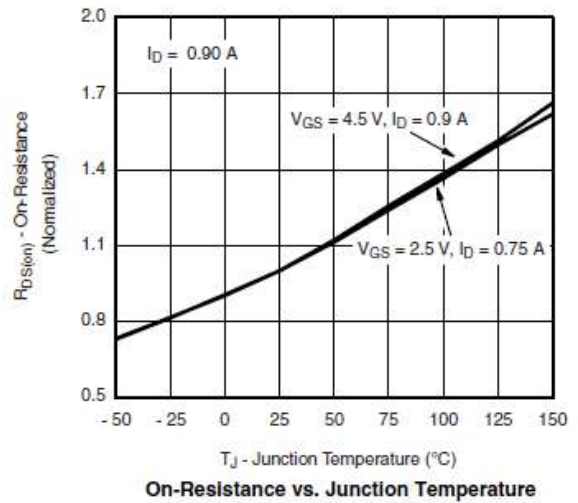
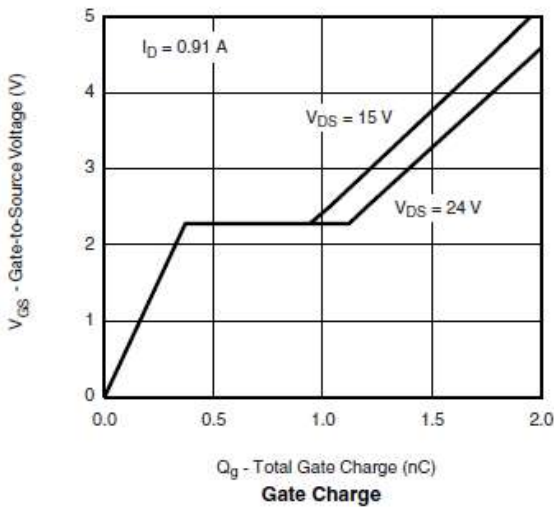
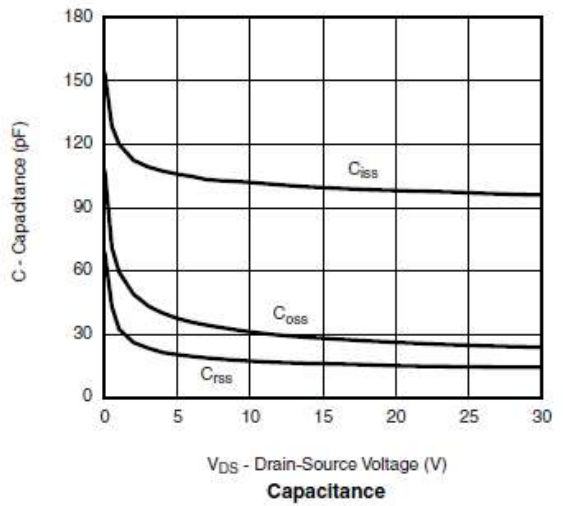
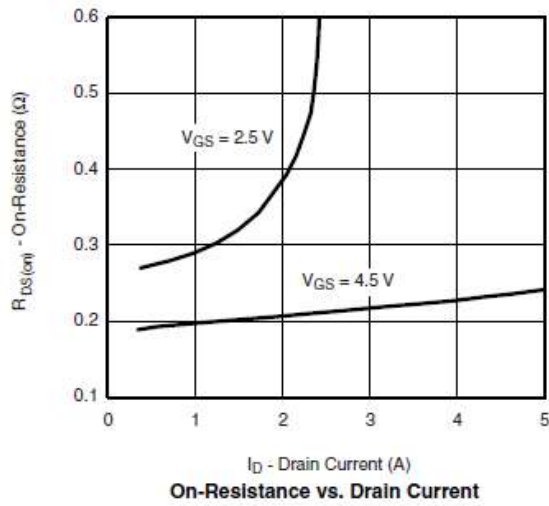
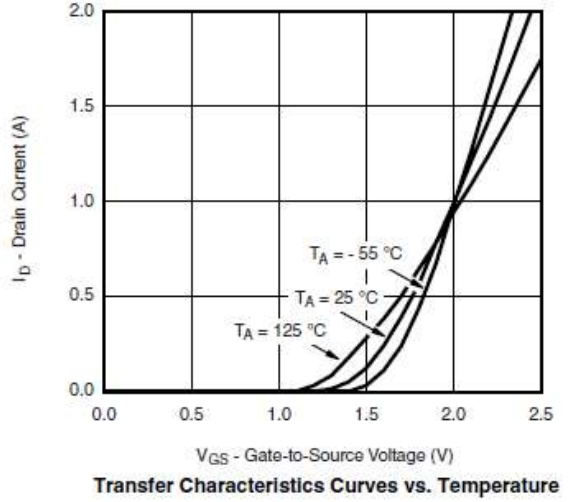
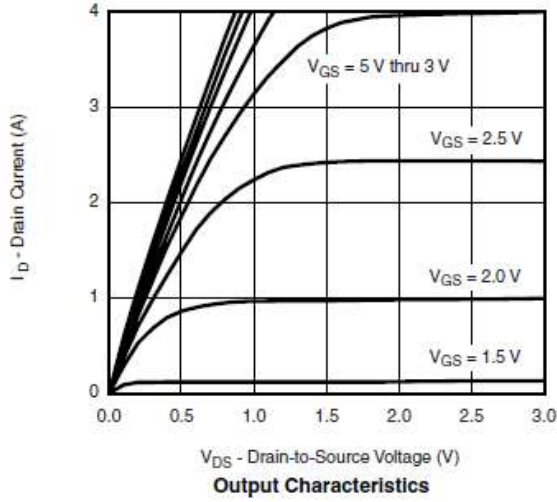
➤ Absolute Maximum Ratings

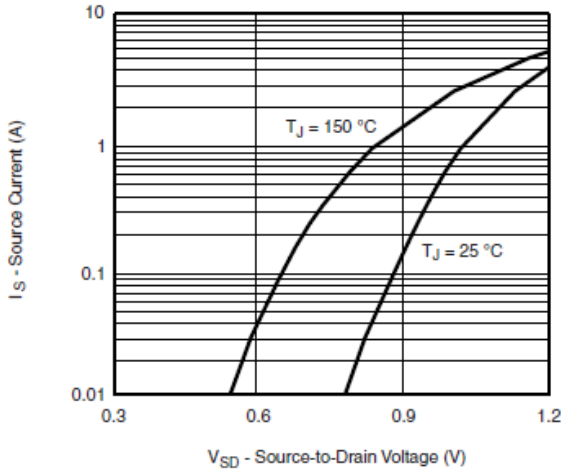
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	30	V
Gate -Source Voltage	V_{GSS}	± 12	V
Continuous Drain Current($T_J=150^\circ C$)	I_D	$T_A=25^\circ C$	0.7
		$T_A=70^\circ C$	0.4
Pulsed Drain Current	I_{DM}	1.0	A
Continuous Source Current(Diode Conduction)	I_S	0.3	A
Power Dissipation	P_D	$T_A=25^\circ C$	0.27
		$T_A=70^\circ C$	0.16
Operating Junction Temperature	T_J	-55/150	$^\circ C$
Storage Temperature Range	T_{STG}	-55/150	$^\circ C$

➤ Electrical Characteristics ($T_A=25^\circ C$ Unless otherwise noted)

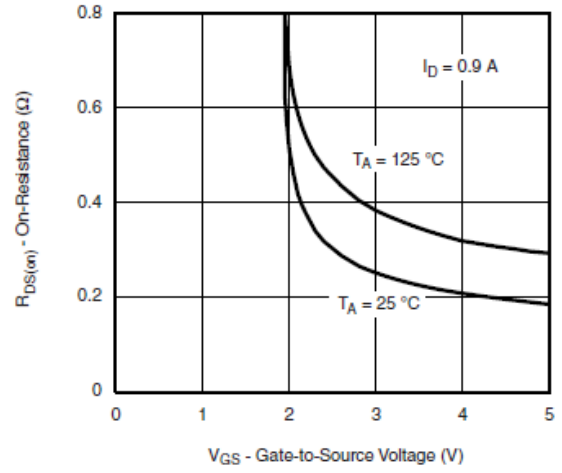
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.5		1.0	
Gate Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 12V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=24V, V_{GS}=0V$			1	uA
		$V_{DS}=24V, V_{GS}=0V$ $T_J=85^\circ C$			5	
On-State Drain Current	$I_{D(on)}$	$V_{DS} \geq 5V, V_{GS}=4.5V$	0.7			A
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=0.6A$		352	440	m Ω
		$V_{GS}=2.5V, I_D=0.5A$		432	500	
		$V_{GS}=1.8V, I_D=0.4A$		620	720	
Forward Transconductance	g_{FS}	$V_{DS}=10V, I_D=0.4A$		1		S
Diode Forward Voltage	V_{SD}	$I_S=0.15A, V_{GS}=0V$		0.6	1.2	V
Dynamic						
Input Capacitance	C_{iss}	$V_{DS}=15V, V_{GS}=0V$ $f=1MHz$		85		pF
Output Capacitance	C_{oss}			25		
Reverse Transfer Capacitance	C_{rss}			15		
Total Gate Charge	Q_g	$V_{DS}=15V, V_{GS}=4.5V$ $I_D=0.6A$		1.4	1.8	nC
Gate-Source Charge	Q_{gs}			0.3		
Gate-Drain Charge	Q_{gd}			0.6		
Turn-On Time	$t_{d(on)}$	$V_{DD}=15V, R_L=20\Omega$ $I_D=0.5A, V_{GEN}=4.5V$ $R_G=1\Omega$		15	25	ns
	t_r			25	45	
Turn-Off Time	$t_{d(off)}$			15	25	
	t_f			10	20	

➤ Typical Characteristics

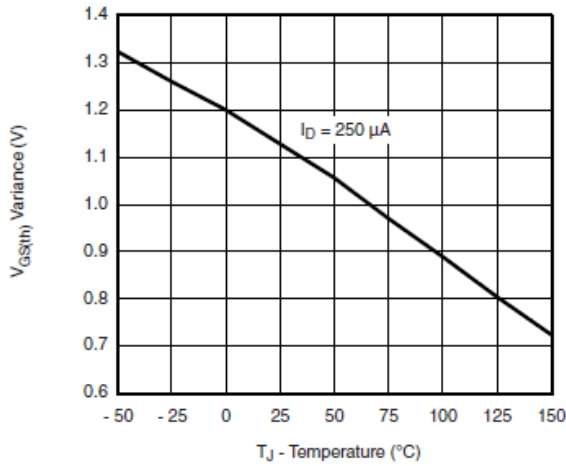




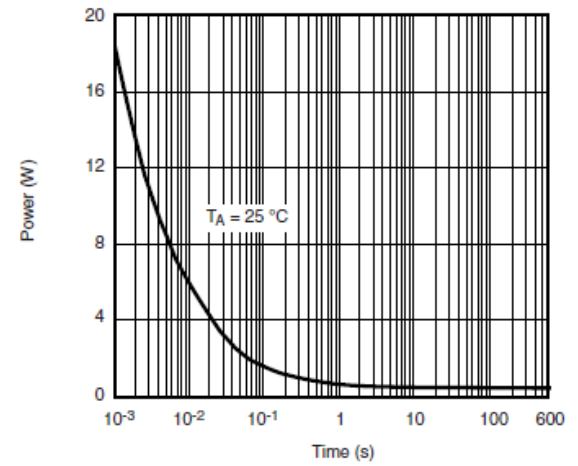
Forward Diode Voltage vs. Temperature



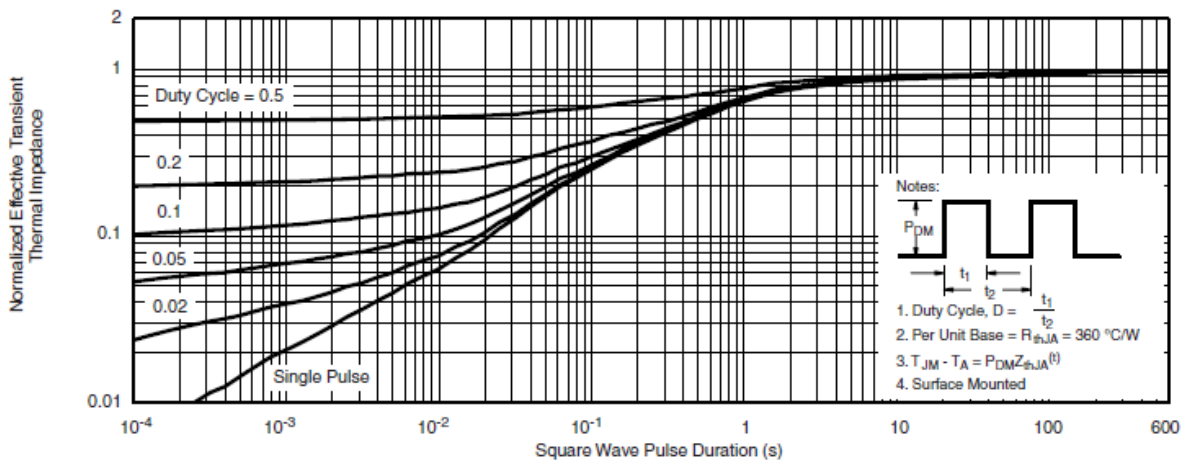
$R_{DS(on)}$ vs. V_{GS} vs. Temperature



Threshold Voltage



Single Pulse Power, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Ambient

- Notes:
- Duty Cycle, $D = \frac{t_1}{t_2}$
 - Per Unit Base = $R_{\theta JA} = 360 \text{ } ^\circ\text{C/W}$
 - $T_{JM} - T_A = P_{DM} Z_{\theta JA}^{(t)}$
 - Surface Mounted

➤ Recommend IR Reflow Soldering Thermal Profile

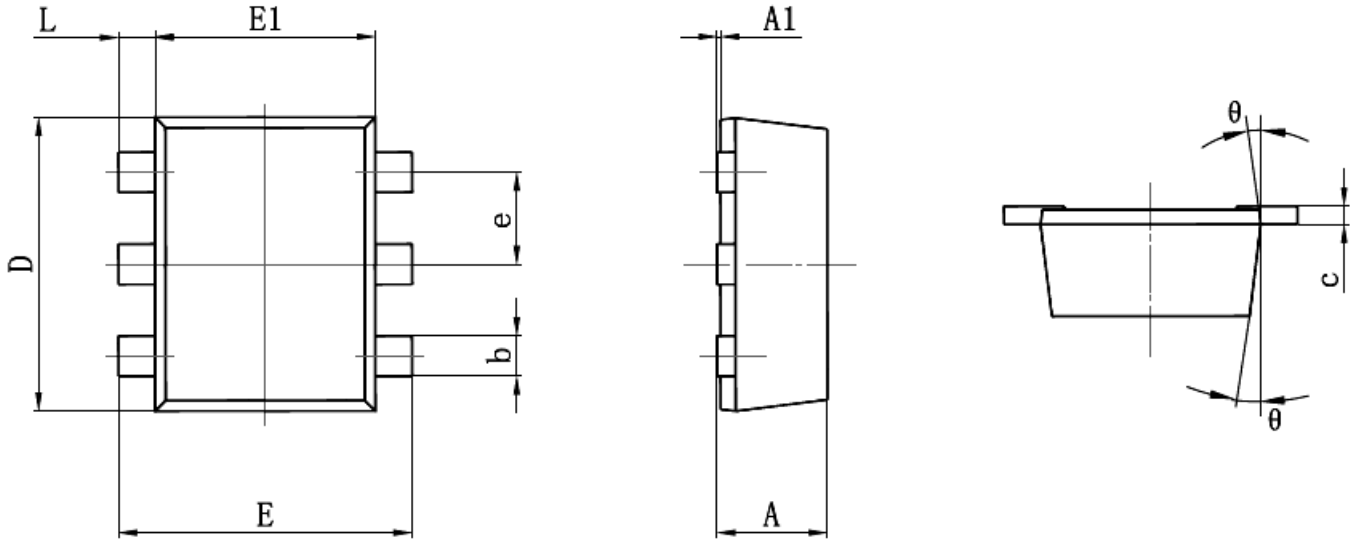


Profile Feature	Pb-Free Assembly Profile
Temperature Min. (T_{smin})	150°C
Temperature Max. (T_{smax})	200°C
Time (t_s) from (T_{smin} to T_{smax})	60-120 seconds
Average Ramp-up Rate (t_L to t_P)	3°C/second max.
Liquidous Temperature (T_L)	217°C
Time (t_L) Maintained Above (T_L)	60 – 150 seconds
Peak Temperature	260°C +0°C / -5°C
Time (t_P) within 5°C of actual Peak Temperature	30 seconds
Ramp-down Rate (T_P to T_L)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.

➤ Ordering Information

Part Number	Description	Quantity
PAN3034L	SOT-563 Reel	3000 pcs

➤ Package Information (SOT-563)



Symbol	Dimenslons In Millimeters		Dimenslons In Inches	
	Min.	Max.	Min.	Max.
A	0.525	0.600	0.021	0.024
A1	0.000	0.050	0.000	0.002
e	0.450	0.550	0.018	0.022
c	0.090	0.160	0.004	0.006
D	1.500	1.700	0.059	0.067
b	0.170	0.270	0.007	0.011
E1	1.100	1.300	0.043	0.051
E	1.500	1.700	0.059	0.067
L	0.100	0.300	0.004	0.012
θ	7 °REF.		7 °REF.	

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